

MSU4N60

600V N-Channel MOSFET

Description

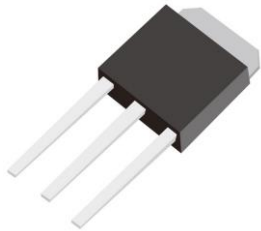
The MSU4N60 is a N-channel enhancement-mode MOSFET, providing the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost effectiveness. The TO-251 package is universally preferred for all commercial-industrial applications

Features

- Low On Resistance
- Simple Drive Requirement
- Low Gate Charge
- Fast Switching Characteristic
- Halogen free package available
- RoHS compliant package

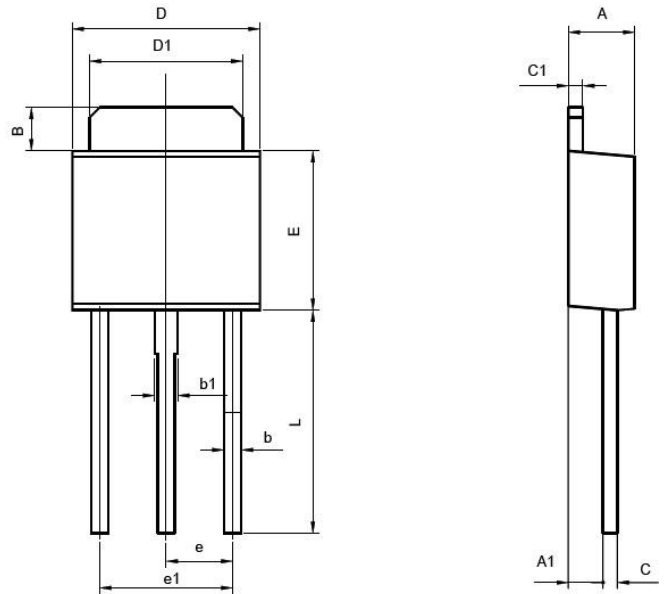
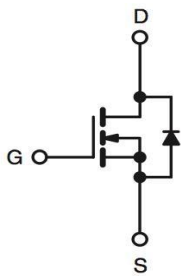
Packing & Order Information

80/Tube ; 4,000/Box



**RoHS
COMPLIANT**

Graphic symbol



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	min	max	min	max
A	2.15	2.45	0.85	0.96
A1	1.00	1.40	0.39	0.55
B	1.25	1.75	0.49	0.69
b	0.45	0.75	0.18	0.3
b1	0.65	0.95	0.26	0.37
C	0.38	0.64	0.15	0.25
C1	0.38	0.64	0.15	0.25
D	6.30	6.70	2.48	2.64
D1	5.10	5.50	2.01	2.17
E	5.30	5.70	2.09	2.24
e	2.3 (typ.)		0.91 (typ.)	
e1	4.4	4.8	1.73	1.89
L	7.4	8.0	2.91	3.15

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MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{DSS}	Drain-Source Voltage	600	V
V _{GS}	Gate-Source Voltage	±30	V
I _D	Drain Current -Continuous (TC=25°C)	4.5	A
	Drain Current -Continuous (TC=100°C)	2.6	A
I _{DM}	Drain Current Pulsed	18	A
E _{AS}	Single Pulsed Avalanche Energy	33	mJ
E _{AR}	Repetitive Avalanche Energy	10	mJ
I _{AR}	Avalanche Current	4.0	A
dV/dt	Peak Diode Recovery dV/dt	4.5	V/ns
P _D	Power Dissipation (TC = 25 °C)	31	W
	- Derate above 25°C	0.25	W/°C
T _{STG}	Operating and Storage Temperature	-55 to +150	°C
T _J	Storage Temperature	150	°C

Note:

1. Repetitive rating; pulse width limited by maximum junction temperature.
2. I_{AS}=4A, V_{DD}=50V, L=8mH, V_G=10V, starting T_J=+25°C.
3. I_{SD}≤4A, di/dt≤100A/μs, V_{DD}≤BVDSS, starting T_J=+25°C.

Thermal Resistance Characteristics

Symbol	Parameter	Max.	Units
R _{θJC}	Thermal Resistance, Junction-to-Case	2.8	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	50	

Static Characteristics

Symbol	Test Conditions	Min	Typ.	Max.	Units
V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2.0	--	4.0	V
R _{DS(ON)}	V _{GS} = 10 V , I _D = 2.25 A	--	2.0	2.5	Ω
BV _{DSS}	V _{GS} = 0 V , I _D =250μA	600	--	--	V
ΔBV _{DSS} / ΔT _J	I _D = 250μA, Referenced to 25°C	--	0.60	--	V/°C
I _{DSS}	V _{DS} = 600 V , V _{GS} = 0 V	--	--	1	μA
	V _{DS} = 480 V , T _C = 125°C	--	--	10	
I _{GSS}	V _{GS} = ±30	--	--	±100	nA

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Dynamic Characteristics					
Symbol	Test Conditions	Min	Typ.	Max.	Units
$t_{d(on)}$	$V_{DD} = 300\text{ V}, I_D = 4.5\text{ A},$ $V_{GS} = 10\text{ V}, R_G = 25\ \Omega$	--	10	30	ns
t_r		--	40	80	ns
$t_{d(off)}$		--	40	100	ns
t_f		--	50	90	ns
Q_g	$V_{DS} = 480\text{ V}, I_D = 4.5\text{ A},$ $V_{GS} = 10\text{ V}$	--	16	--	nC
Q_{gs}		--	2.5	--	nC
Q_{gd}		--	6.5	--	nC
C_{ISS}	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $F = 1.0\text{ MHz}$	--	560	--	pF
C_{OSS}		--	55	--	pF
C_{RSS}		--	7	--	pF

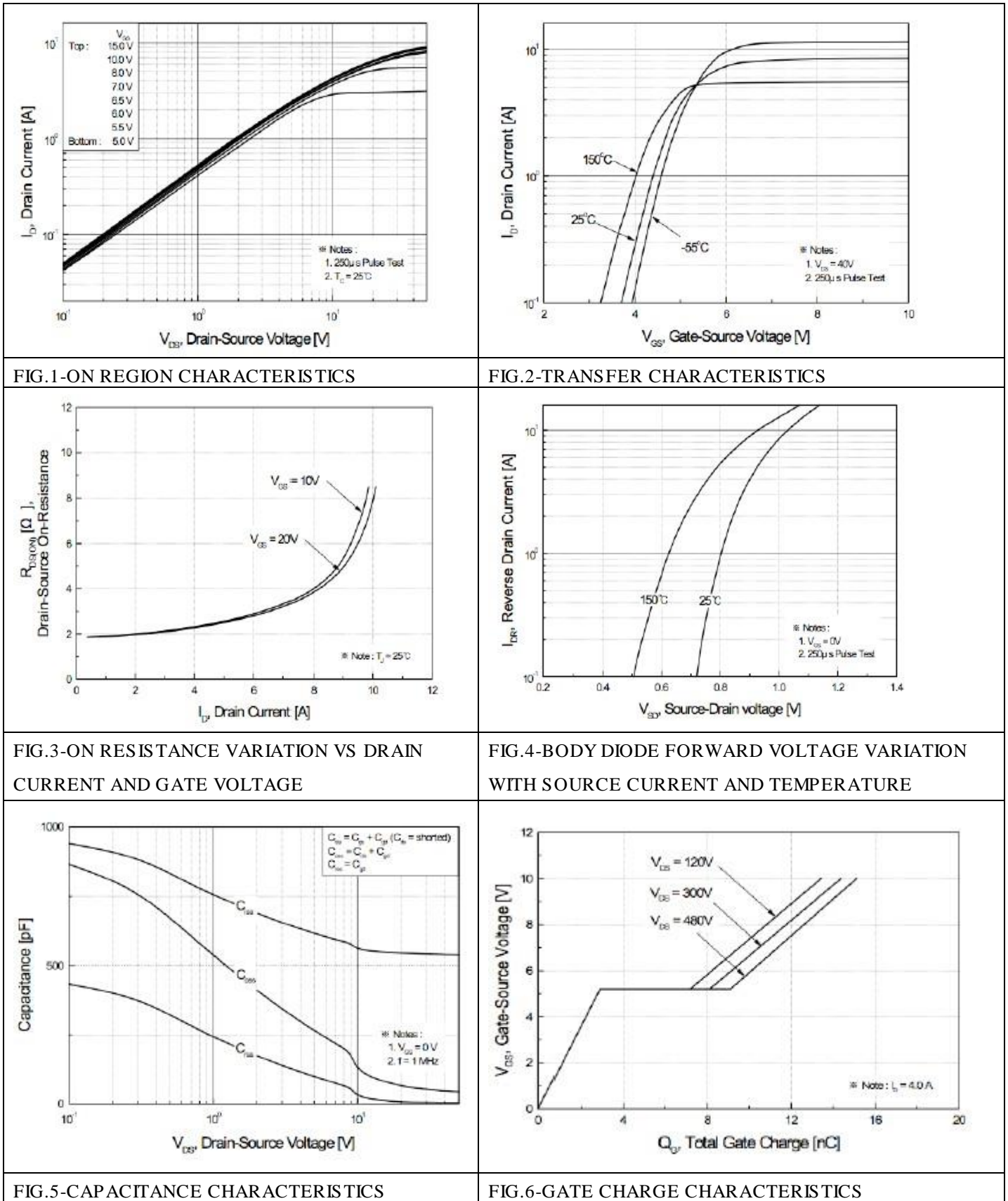
Source-Drain Diode Maximum Ratings and Characteristics						
Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
I_S			--	--	4.0	A
I_{SM}			--	--	16	
V_{SD}	$I_S = 4\text{ A}, V_{GS} = 0\text{ V}$		--	--	1.4	V
t_{rr}	$I_S = 4\text{ A}, V_{GS} = 0\text{ V}$		--	270	--	ns
Q_{rr}	$diF/dt = 100\text{ A}/\mu\text{s}$		--	18	--	uC

*Pulse Test : Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

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Characteristics Curve



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Characteristics Curve

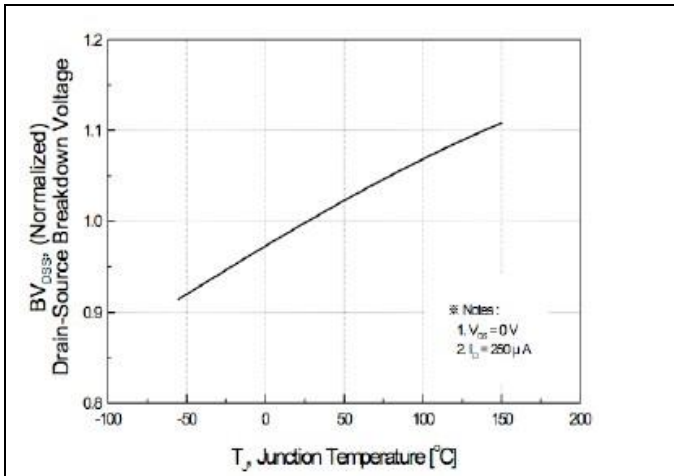


FIG.7-BREAKDOWN VOLTAGE VARIATION VS TEMPERATURE

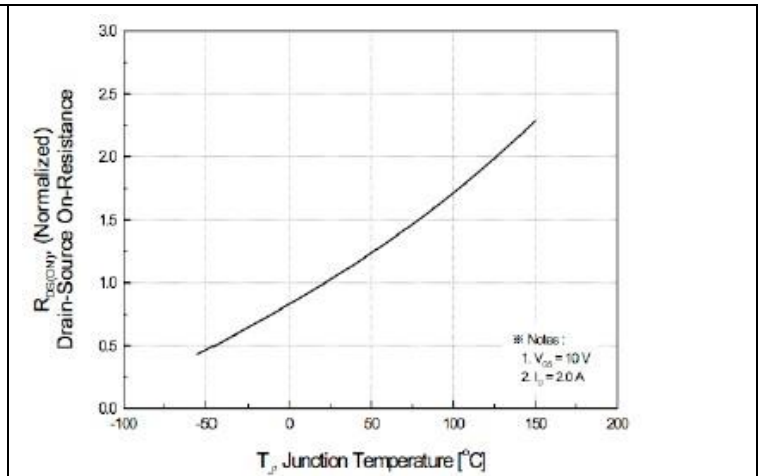


FIG.8-ON-RESISTANCE VARIATION VS TEMPERATURE

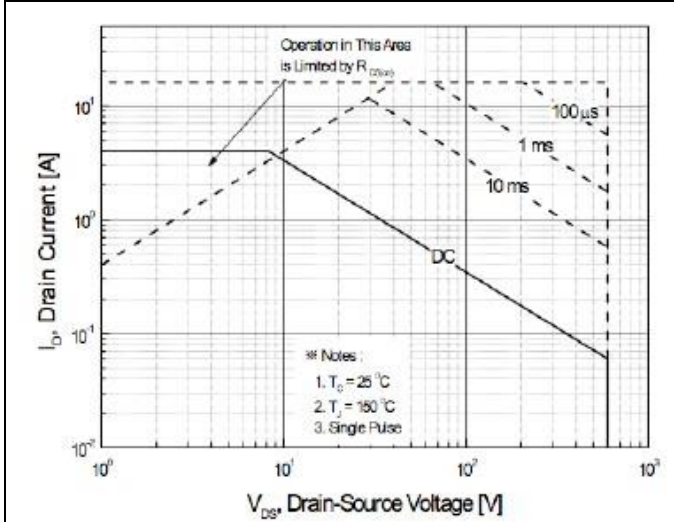


FIG.9-MAXIMUM SAFE OPERATING AREA

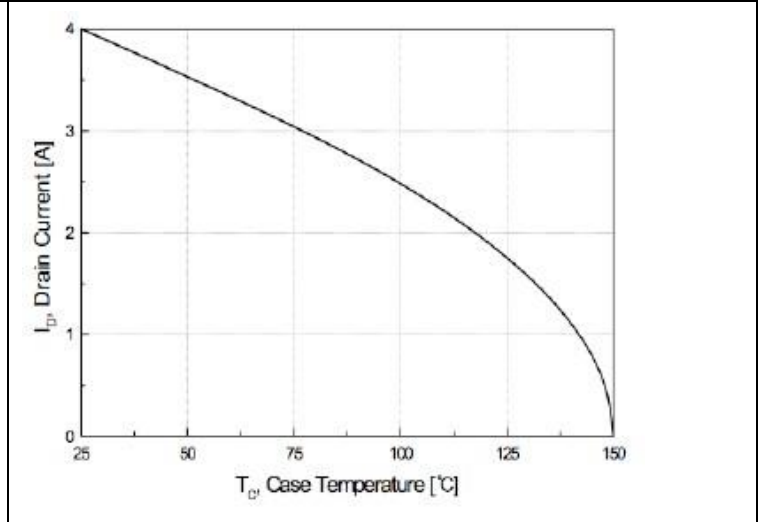


FIG.10-MAXIMUM DRAIN CURRENT VS CASE TEMPERATURE

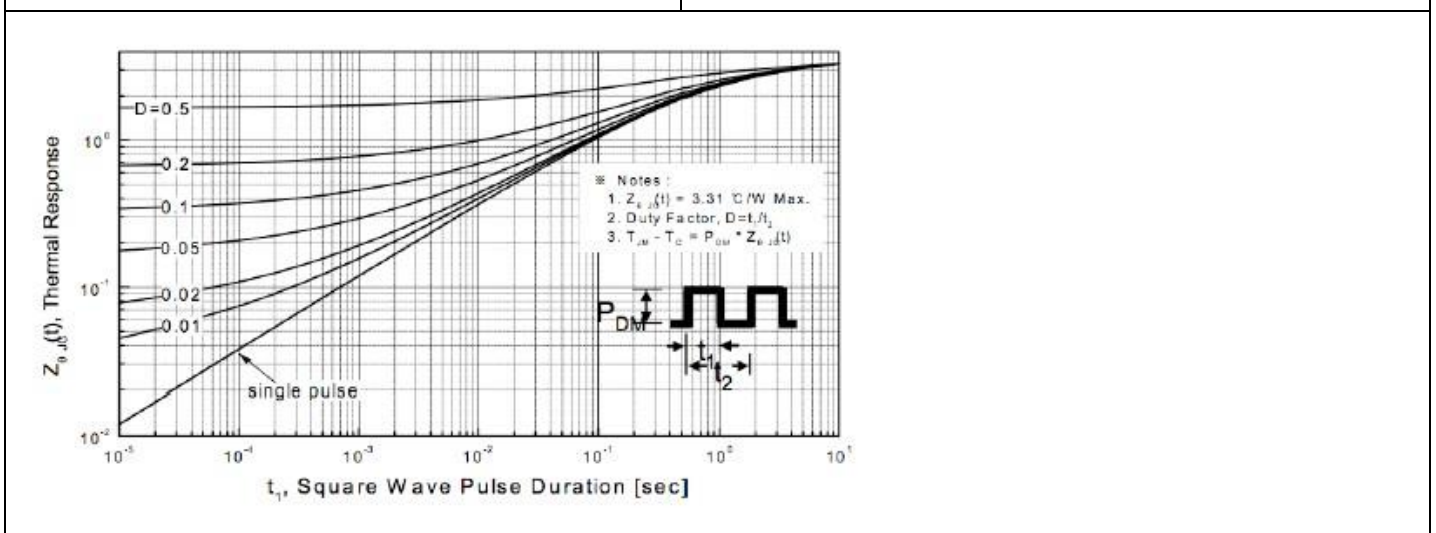


FIG.11-TRANSIENT THERMAL RESPONSE CURVE

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■ Characteristics Test Circuit & Waveform

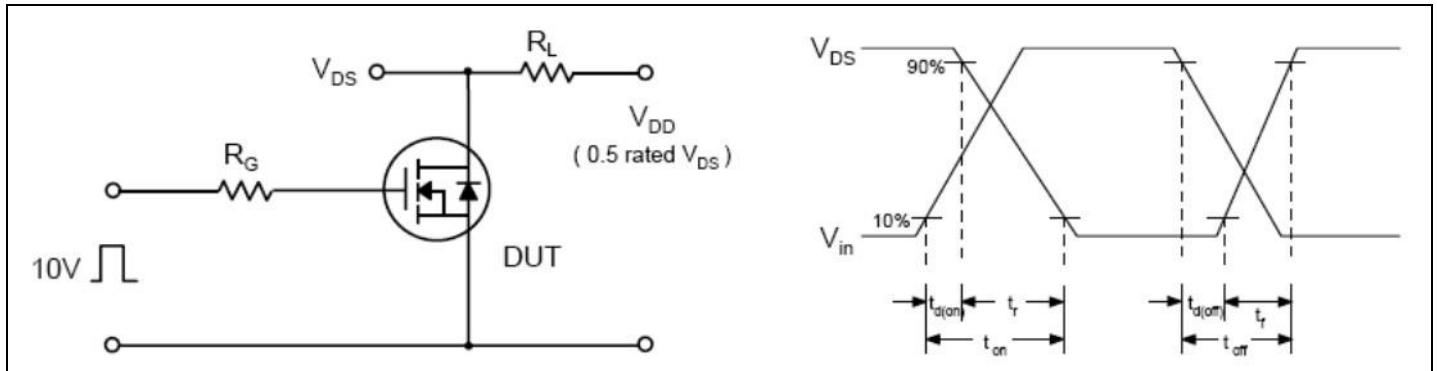


FIG.12-RESISTIVE SWITCHING TEST CIRCUIT & WAVEFORMS

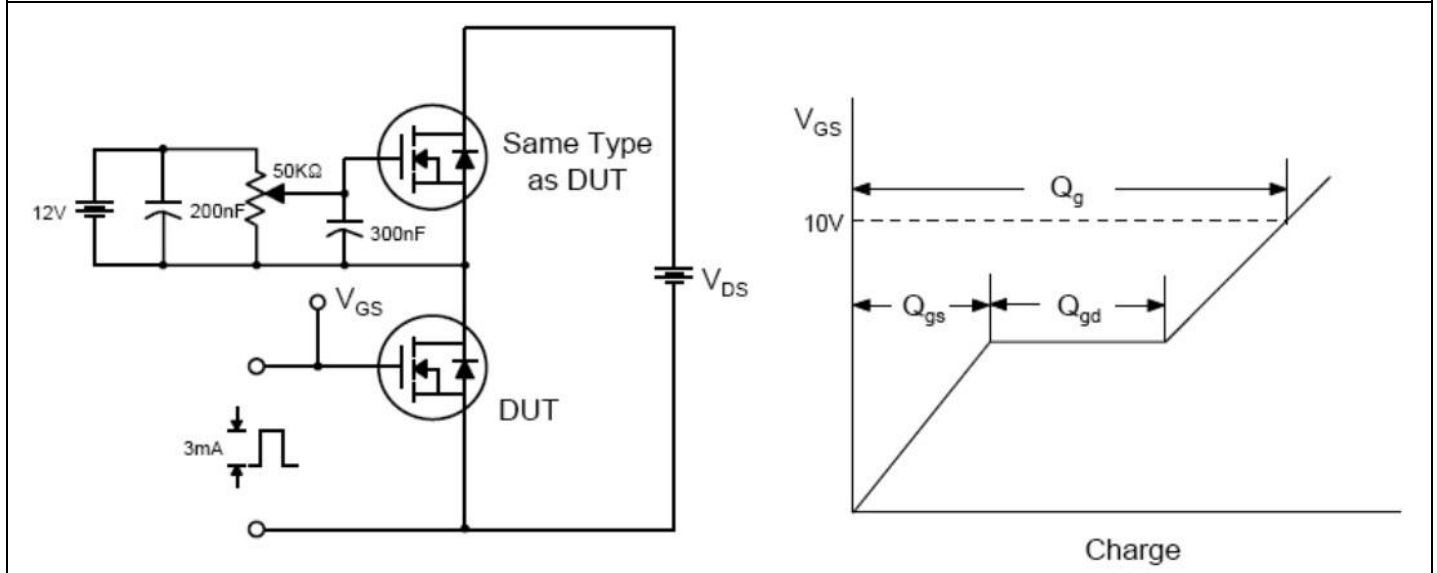


FIG.13-GATE CHARGE TEST CIRCUIT & WAVEFORM

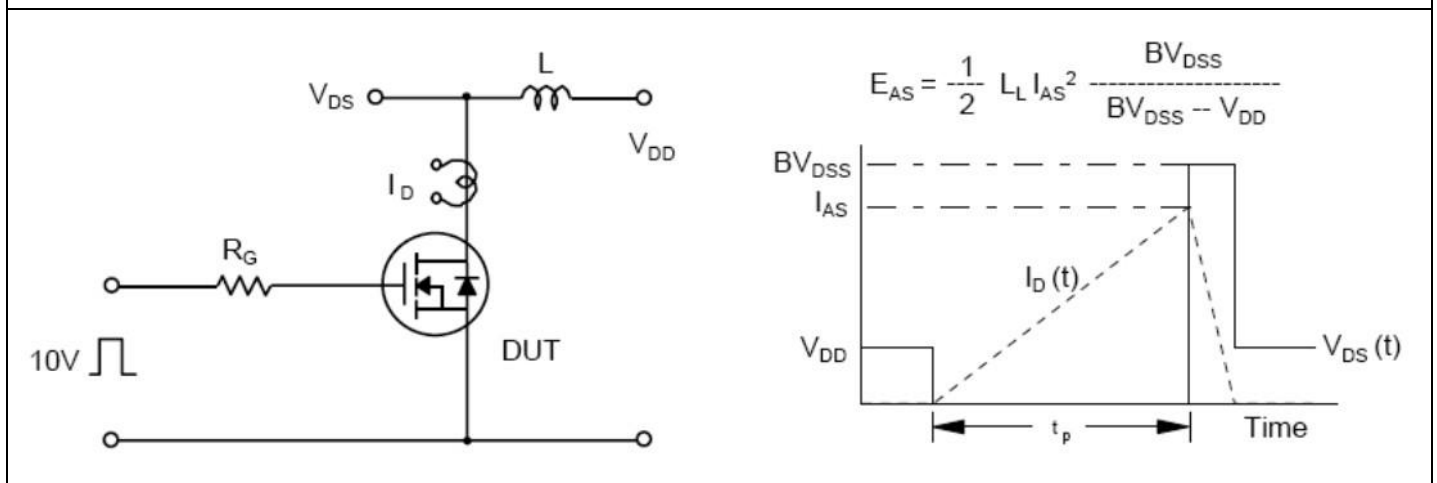


FIG.14-UNCLAMPED LINDUCTIVE SWITCHING TEST CIRCUIT & WAVEFORMS

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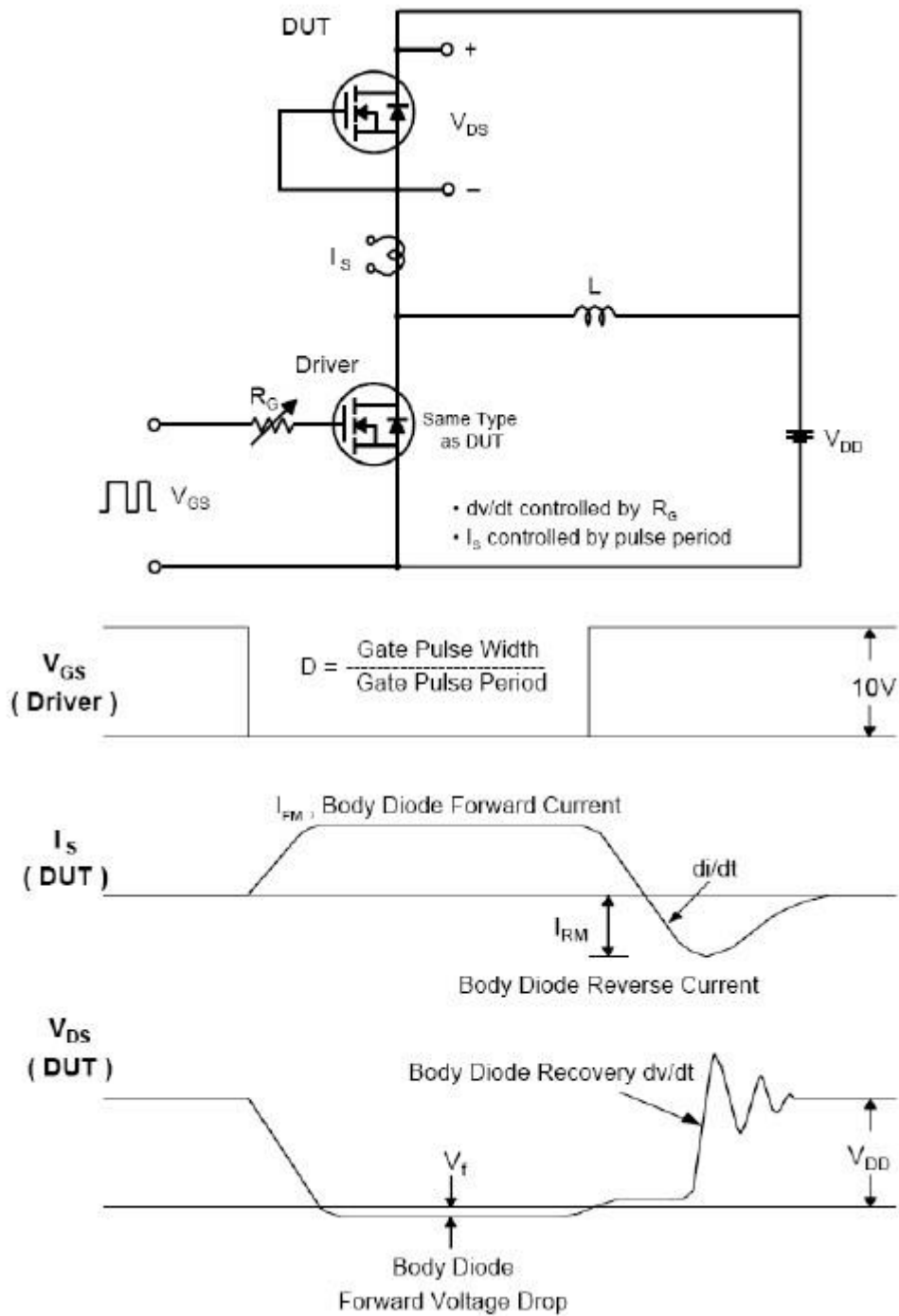


Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

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